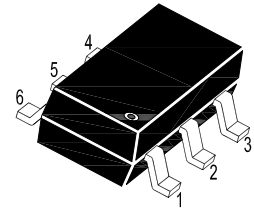
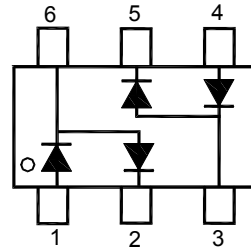


BAV99DW-HAF

Silicon Epitaxial Planar Switching Diode

Features

- Halogen and Antimony Free(HAF), RoHS compliant



1. A1 2. C1 3. AC2
4. A2 5. C2 6. AC1
Marking Code: A7
SOT-363 Plastic package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	100	V
Reverse Voltage	V_R	100	V
Continuous Forward Current	I_F	150	mA
Single Diode Load		130	
Double Diode Load			
Repetitive Peak Forward Current	I_{FRM}	500	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	4	A
at $t = 1 \mu\text{s}$		1	
at $t = 1 \text{ ms}$		0.5	
at $t = 1 \text{ s}$			
Total Power Dissipation	P_{tot}	200	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	625	$^\circ\text{C}/\text{W}$
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage	V_F	0.715	V
at $I_F = 1 \text{ mA}$		0.855	
at $I_F = 10 \text{ mA}$		1	
at $I_F = 50 \text{ mA}$		1.25	
Reverse Current	I_R	30	nA
at $V_R = 25 \text{ V}$		0.5	μA
at $V_R = 80 \text{ V}$		30	μA
at $V_R = 25 \text{ V}, T_j = 150^\circ\text{C}$		50	μA
Diode Capacitance	C_d	1.5	pF
at $V_R = 0, f = 1 \text{ MHz}$			
Reverse Recovery Time	t_{rr}	4	ns
at $I_F = I_R = 10 \text{ mA}, I_{rr} = 0.1 \times I_R, R_L = 100 \Omega$			

